

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An image sensor comprising:
a plurality of pixels formed in a semiconductor substrate, each pixel including a light sensitive element;
a micro-lens over each of said light sensitive elements; and
a layer of oxide disposed between the light sensitive elements and the micro-lenses, wherein the layer of oxide includes raised ridge structures formed from the layer of oxide surrounding each of said micro-lenses, wherein each said raised ridge structure has a triangular cross-section and at least partially supports said micro-lens, wherein the micro-lens overlays a base portion of the raised ridge structure.
2. (Original) The image sensor of Claim 1 wherein said raised ridge structure is circular.
3. (Previously Presented) The image sensor of Claim 1 wherein said raised ridge structure confines said micro-lens.
4. (Original) The image sensor of Claim 1 wherein the micro-lenses are formed from polymethylmethacrylate (PMMA) or polyglycidylmethacrylate (PGMA).
5. (Previously Presented) The image sensor of Claim 1 wherein said raised ridge structure has a height of about 0.2 microns.
6. (Cancelled)
7. (Original) The image sensor of Claim 1 further including a color filter layer between said micro-lenses and said light sensitive elements.

8. (Currently Amended) A pixel of an image sensor comprising:
a light sensitive element formed in a semiconductor substrate;
a micro-lens over said light sensitive element; and
a layer of oxide disposed between the light sensitive element and the micro-lens,
wherein the layer of oxide includes a raised ridge structure formed from the layer of
oxide surrounding said micro-lens, wherein said raised ridge structure has a triangular
cross-section and at least partially supports said micro-lens, wherein the micro-lens
overlays a base portion of the raised ridge structure.

9. (Original) The pixel of Claim 8 wherein said raised ridge structure is
circular.

10. (Previously Presented) The pixel of Claim 8 wherein said raised ridge
structure confines said micro-lens.

11. (Original) The pixel of Claim 8 wherein the micro-lens is formed from
polymethylmethacrylate (PMMA) or polyglycidylmethacrylate (PGMA).

12. (Previously Presented) The pixel of Claim 8 wherein said raised ridge
structure has a height of about 0.2 microns.

13. (Cancelled)

14. (Original) The pixel of Claim 8 further including a color filter layer
between said micro-lens and said light sensitive element.

15. (Currently Amended) A method of forming a pixel of an image sensor
comprising:

forming a light sensitive element in a semiconductor substrate;

forming a top planarizing layer of oxide over said light sensitive element;

isotropically dry etching the top planarizing layer of oxide to form a raised ridge structure ~~over~~ from said top planarizing layer, said raised ridge structure encompassing said light sensitive element; and

forming a microlens within the interior of said raised ridge structure and over said light sensitive element, wherein said raised ridge structure has a triangular cross-section and at least partially supports said micro-lens, wherein the micro-lens overlays a base portion of the raised ridge structure.

16. (Cancelled)

17. (Previously Presented) The method Claim 15 wherein said raised ridge structure confines said micro-lens.

18. (Original) The method of Claim 15 wherein said raised ridge structure is a closed shape.

19. (Original) The method of Claim 15 further including forming a color filter layer between said micro-lens and said light sensitive element.